Abstracts

A new dynamic electro-thermal nonlinear model for silicon RF LDMOS FETs

W.R. Curtice, J.A. Pla, D. Bridges, T. Liang and E.E. Shumate. "A new dynamic electro-thermal nonlinear model for silicon RF LDMOS FETs." 1999 MTT-S International Microwave Symposium Digest 99.2 (1999 Vol. II [MWSYM]): 419-422 vol.2.

The development and behavior of a new model for Motorola's LDMOS transistor is described. The model includes self-heating effects, produces accurate small-signal simulations as well as large-signal, harmonic-balance simulations and also operates in the transient mode. It is simpler than previous models, yet it accurately predicts mixed signal effects, such as intermodulation distortion.

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